

TIP47G, TIP48G, TIP50G

High Voltage NPN Silicon Power Transistors

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

Features

- Popular TO-220 Plastic Package
- Complementary to the MJE5730 and MJE5731 Series
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	TIP47	TIP48	TIP50	Unit
Collector – Emitter Voltage	V_{CEO}	250	300	400	Vdc
Collector – Base Voltage	V_{CB}	350	400	500	Vdc
Emitter – Base Voltage	V_{EB}	5.0			Vdc
Collector Current – Continuous	I_C	1.0			Adc
Collector Current – Peak	I_{CM}	2.0			Adc
Base Current	I_B	0.6			Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32			W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016			W W/ $^\circ\text{C}$
Unclamped Inducting Load Energy (See Figure 8)	E	20			mJ
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150			$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

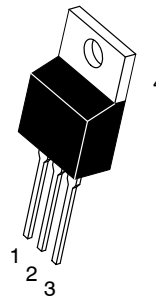
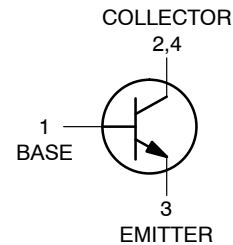
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$



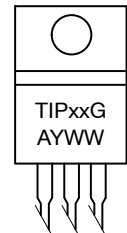
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POWER TRANSISTORS
NPN SILICON
250 – 300 – 400 VOLTS
40 WATTS**



MARKING DIAGRAM



**TO-220AB
CASE 221A
STYLE 1**

TIPxx = Device Code
 xx = 47, 48, or 50
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 30\text{ mA}$, $I_B = 0$)	TIP47 TIP48 TIP50	$V_{CEO(sus)}$	250 300 400	– – –	Vdc
Collector Cutoff Current ($V_{CE} = 150\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 200\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 300\text{ Vdc}$, $I_B = 0$)	TIP47 TIP48 TIP50	I_{CEO}	– – –	1.0 1.0 1.0	mAdc
Collector Cutoff Current ($V_{CE} = 350\text{ Vdc}$, $V_{BE} = 0$) ($V_{CE} = 400\text{ Vdc}$, $V_{BE} = 0$) ($V_{CE} = 500\text{ Vdc}$, $V_{BE} = 0$)	TIP47 TIP48 TIP50	I_{CES}	– – –	1.0 1.0 1.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	–	1.0	mAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 0.3\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	30 10	150 –	–
Collector–Emitter Saturation Voltage ($I_C = 1.0\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	$V_{CE(sat)}$	–	1.0	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$)	$V_{BE(on)}$	–	1.5	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 0.1\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 2.0\text{ MHz}$)	f_T	10	–	MHz
Small–Signal Current Gain ($I_C = 0.2\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	25	–	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping
TIP47G	TO–220 (Pb–Free)	50 Units / Rail
TIP48G	TO–220 (Pb–Free)	50 Units / Rail
TIP49G	TO–220 (Pb–Free)	50 Units / Rail
TIP50G	TO–220 (Pb–Free)	50 Units / Rail

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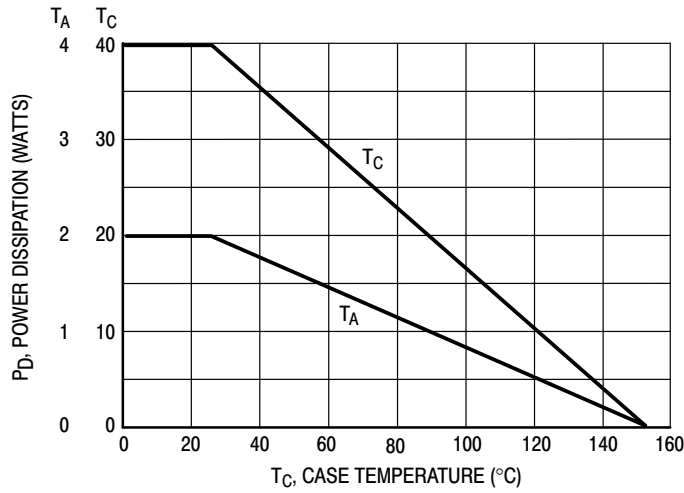
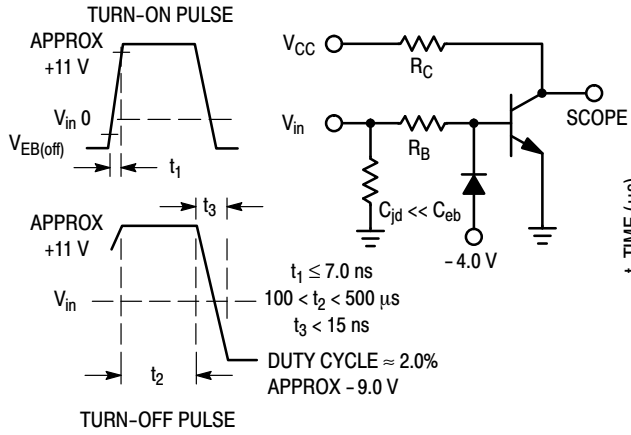


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 2. Switching Time Equivalent Circuit

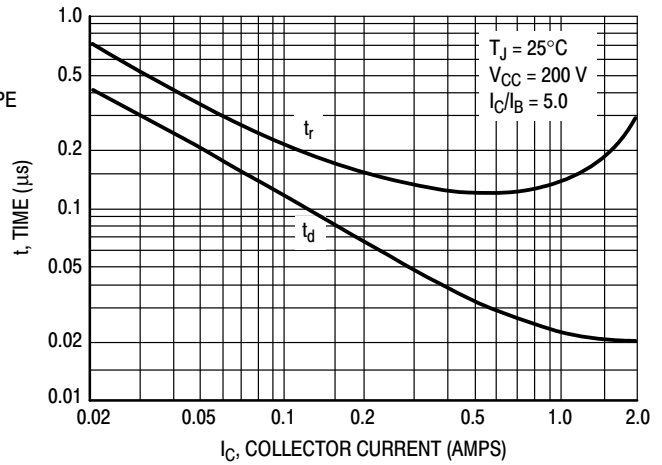


Figure 3. Turn-On Time

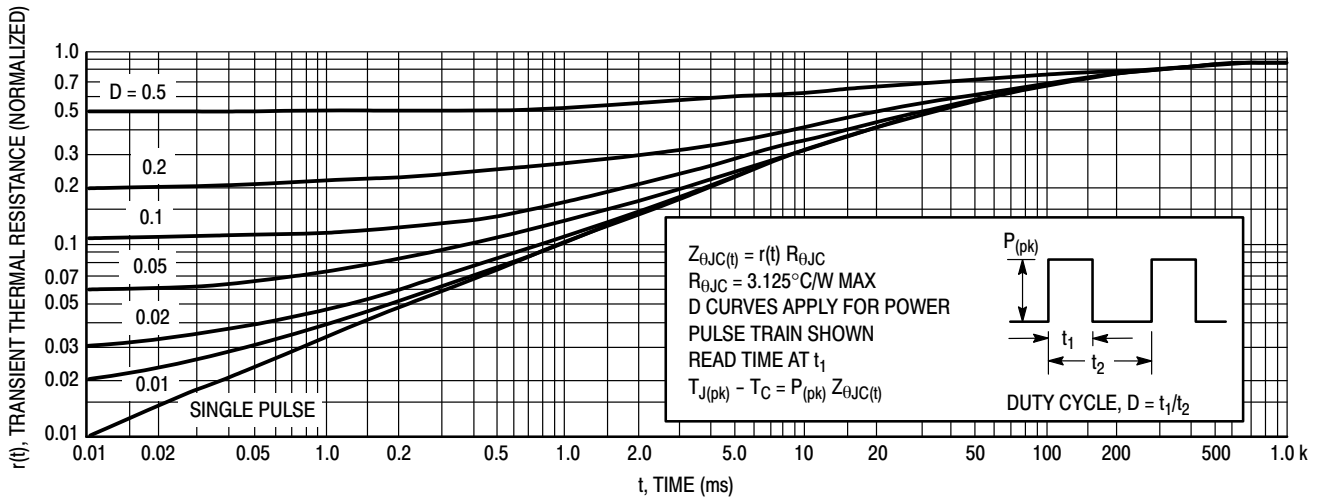


Figure 4. Thermal Response

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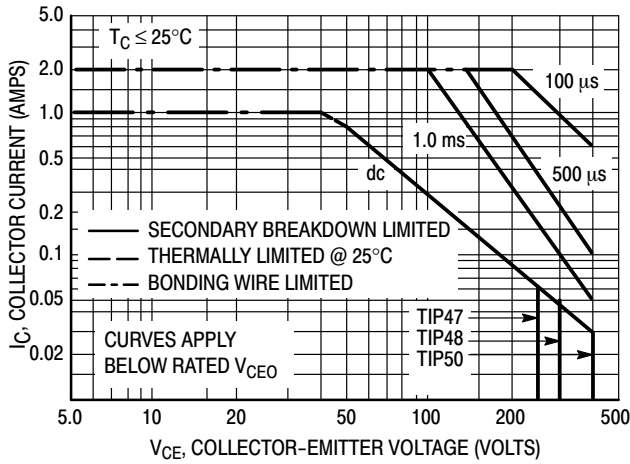


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

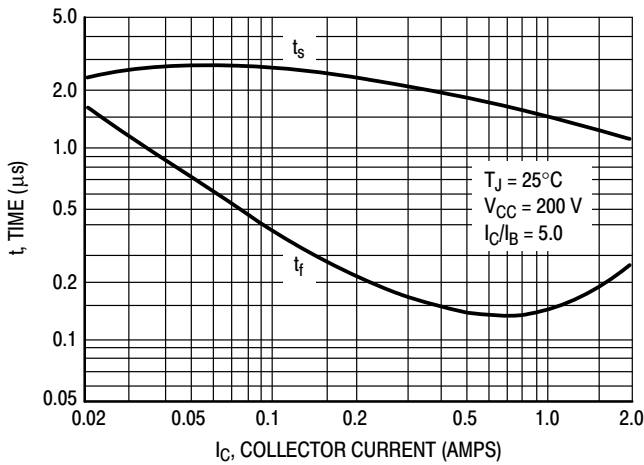


Figure 6. Turn-Off Time

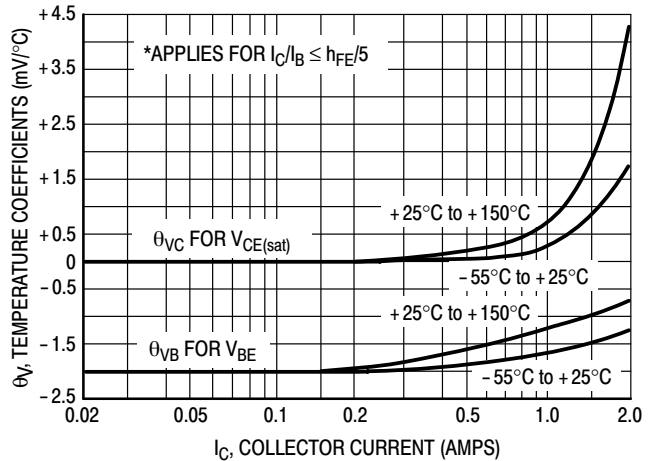
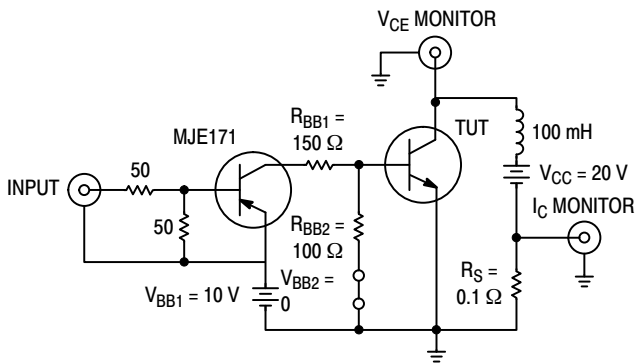


Figure 7. Temperature Coefficients



Note A: Input pulse width is increased until $I_{CM} = 0.63 \text{ A}$.

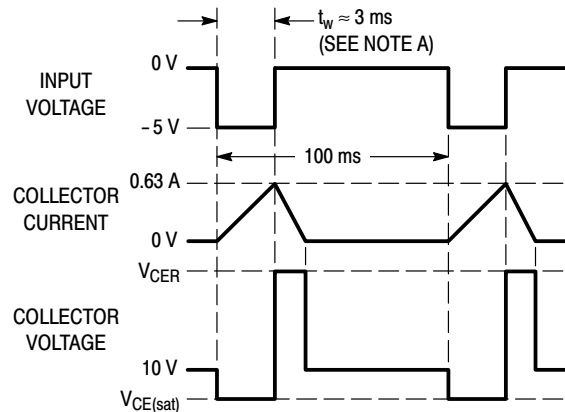


Figure 8. Inductive Load Switching

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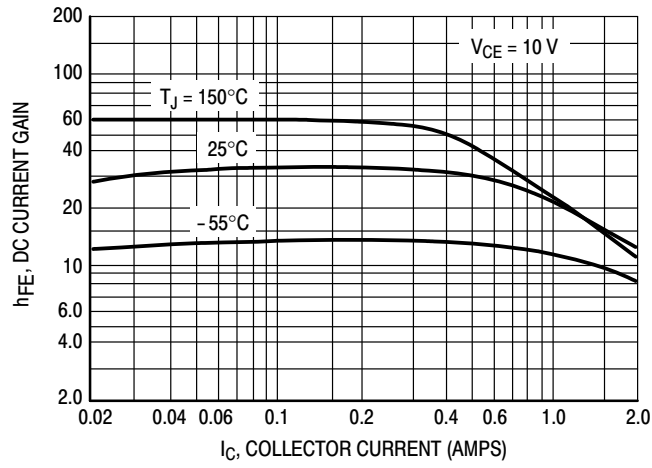


Figure 9. DC Current Gain

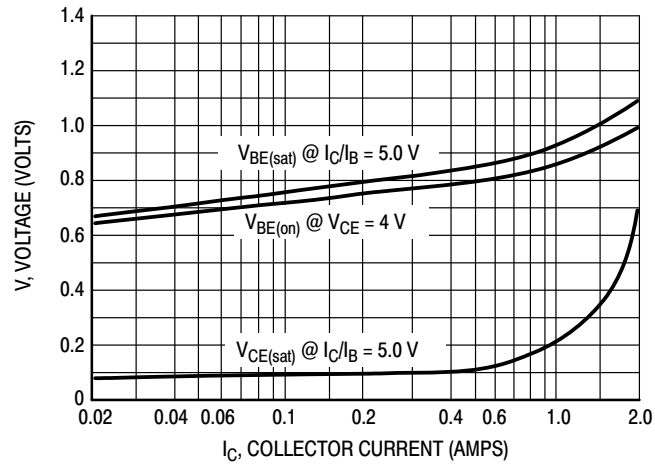
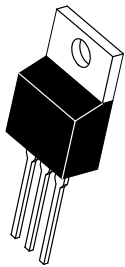
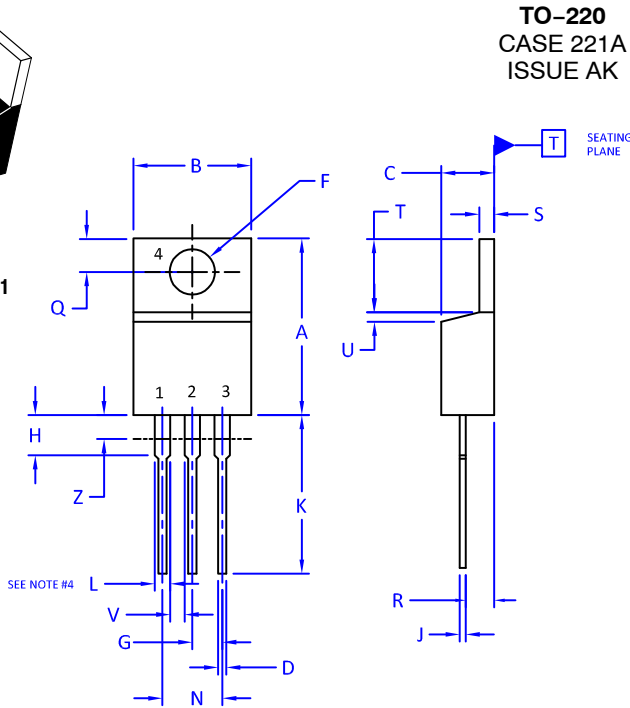


Figure 10. "On" Voltages

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1



TO-220 CASE 221A ISSUE AK

DATE 13 JAN 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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